AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

- 1.-35. (Canceled)
- 36. (Currently Amended) A method for polishing a substrate comprising a metal in an oxidized form, the method comprising the steps of:
- (a) providing a substrate comprising a metal in an oxidized form, wherein the metal is a noble metal selected from the group consisting of platinum, iridium, ruthenium, rhodium, palladium, silver, osmium, gold, and combinations thereof,
- (b) contacting a portion of the substrate with a chemical-mechanical polishing system comprising:
 - (i) a polishing component selected from the group consisting of an abrasive, a polishing pad, and a combination thereof,
 - (ii) about 0.1 to about 1 wt.% of a reducing agent based on the weight of the liquid carrier and any components dissolved or suspended therein, wherein the reducing agent is being selected from the group consisting of 3-hydroxy 4 pyrones, α hydroxy γ butyrolactones, ascorbic acid, borane, borohydrides, dialkylamine boranes, hydrogen, hydroquinones, hypophosphorous acid, trihydroxybenzenes, solvated electrons, sulfurous acid, salts thereof, and mixtures thereof, and
 - (iii) a liquid carrier, and
- (c) abrading at least a portion of the metal in an oxidized form to polish the substrate.
- 37. (Currently Amended) The method of claim 36, wherein the chemical-mechanical polishing system comprises about 0.1 to about 0.5 wt.% reducing agent ascorbic acid based on the weight of the liquid carrier and any components dissolved or suspended therein.

38.-39. (Canceled)

41. (Previously Presented) The method of claim 36, wherein the polishing system has a pH of about 1 to about 7.

42.-43. (Canceled)

- 44. (New) The method of claim 41, wherein the chemical-mechanical polishing system has a pH of about 2 to about 5.
- 45. (New) The method of claim 36, wherein the oxidized form is selected from the group consisting of oxides, nitrides, borides, sulfides, and mixtures thereof.
- 46. (New) The method of claim 45, wherein the oxidized form is an oxide, and the metal in an oxidized form has a molecular formula M_xO_y in which M represents the metal and x and y represent integers, where y is greater than or equal to x.
- 47. (New) The method of claim 46, wherein the metal in an oxidized form is iridium oxide.
- 48. (New) The method of claim 36, wherein the chemical-mechanical polishing system comprises an abrasive suspended in the liquid carrier, and the abrasive comprises a metal oxide selected from the group consisting of alumina, silica, ceria, zirconia, titania, germania, co-formed products thereof, and combinations thereof.
- 49. (New) The method of claim 48, wherein the abrasive comprises silica, fumed alumina, or a combination thereof.
 - 50. (New) The method of claim 48, wherein the abrasive comprises α -alumina.
- 51. (New) The method of claim 50, wherein the abrasive further comprises fumed alumina.
- 52. (New) The method of claim 50, wherein α -alumina comprises about 60 wt.% or more of the abrasive based on the total weight of the abrasive.

- 53. (New) The method of claim 51, wherein α-alumina comprises about 60 wt.% or more of the abrasive based on the total weight of the abrasive.
- 54. (New) The method of claim 36, wherein the chemical-mechanical polishing system further comprises a complexing agent.
- 55. (New) The method of claim 36, wherein the chemical-mechanical polishing system further comprises a pH buffering agent.
- 56. (New) The method of claim 36, wherein the chemical-mechanical polishing system further comprises a surfactant.
 - 57. (New) The method of claim 36, wherein the liquid carrier is water.
- 58. (New) The method of claim 57, wherein the oxidized form is selected from the group consisting of oxides, nitrides, borides, sulfides, and mixtures thereof.
- 59. (New) The method of claim 58, wherein the oxidized form is an oxide, and the metal in an oxidized form has a molecular formula M_xO_y in which M represents the metal and x and y represent integers, where y is greater than or equal to x.
- 60. (New) The method of claim 59, wherein the metal in an oxidized form is iridium oxide.
- 61. (New) The method of claim 57, wherein the chemical-mechanical polishing system comprises an abrasive suspended in the liquid carrier, and the abrasive comprises a metal oxide selected from the group consisting of alumina, silica, ceria, zirconia, titania, germania, co-formed products thereof, and combinations thereof.
- 62. (New) The method of claim 61, wherein the abrasive comprises silica, fumed alumina, or a combination thereof.
 - 63. (New) The method of claim 61, wherein the abrasive comprises α-alumina.
- 64. (New) The method of claim 63, wherein the abrasive further comprises fumed alumina.

- 65. (New) The method of claim 63, wherein α -alumina comprises about 60 wt.% or more of the abrasive based on the total weight of the abrasive.
- 66. (New) The method of claim 64, wherein α-alumina comprises about 60 wt.% or more of the abrasive based on the total weight of the abrasive.
- 67. (New) The method of claim 57, wherein the chemical-mechanical polishing system further comprises a complexing agent.
- 68. (New) The method of claim 57, wherein the chemical-mechanical polishing system further comprises a pH buffering agent.
- 69. (New) The method of claim 57, wherein the chemical-mechanical polishing system further comprises a surfactant.
- 70. (New) The method of claim 57, wherein the chemical-mechanical polishing system has a pH of about 2 to about 5.